

AMENDMENTS TO THE SPECIFICATION:

Please amend the specification at page 1, line 4 as follows:

Description BACKGROUND OF THE INVENTION

Please amend the specification at page 1, line 11 as follows:

~~Background of the invention~~ Description of Related Art

Please add the following paragraphs to the specification at page 3, line 1:

Document EP 0 280 905 describes a process for producing pressure sensors in which a borosilicate glass layer is formed on a silicon wafer. The glass layer is described as a matrix which covers the corresponding sensor chips and a conductive layer. However, the borosilicate glass layer is formed by sputtering on the surface of the silicon sensor wafer. It is fundamentally difficult and expensive to produce relatively great layer thicknesses by sputtering. Although a layer thickness of 5 μm is mentioned, when using the sputtering process this is typically associated with considerable heating of the substrate, which can cause further difficulties.

Document US 5,825,233 describes a microhousing for infrared chips, in which a layer of soldering agent is applied by vacuum deposition and lift-off technique or etching or by a mask. However, a soldering agent brings with it the risk of contamination.

The document "Anodic Bonding Technique under Low-temperature and Low-voltage using Evaporated Glass" by Woo-Beom Choi, 9th International Vacuum Microelectronics Conference, St. Petersburg, 1996 describes a process in which a glass layer is applied to a silicon wafer by electron beam evaporation. However, the application of this process is limited.

Please amend the specification at page 3, line 5 as follows:

General description of the invention BRIEF SUMMARY OF THE INVENTION